

Features

- High density cell design for ultra low $R_{DS(on)}$
- Fully characterized avalanche voltage and current
- Excellent package for good heat dissipation

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
-60V	35mΩ@-10V	-10A
	50mΩ@-4.5V	

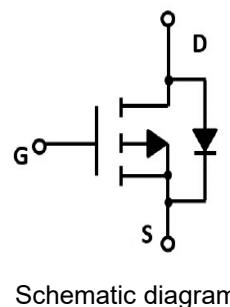
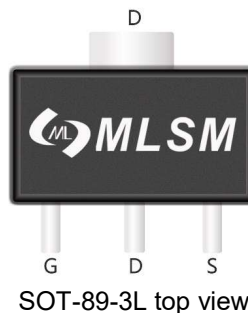
Application

- PWM applications
- Power management
- Load switch



0G10AP : Device code
 XXXX : Code

Marking and pin assignment



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-60	V
V_{GS}	Gate-Source Voltage	±20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_c=25^{\circ}\text{C}$ -10	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_c=25^{\circ}\text{C}$ -40	A
I_D	Continuous Drain Current	$T_c=25^{\circ}\text{C}$ -10	A
P_D	Maximum Power Dissipation	$T_c=25^{\circ}\text{C}$ 1.7	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	315	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MZ0G10AP	SOT-89-3L	0G10AP	1,000	10,000	40,000	7"reel

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
BV(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=-250μA	-60	–	–	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V, VGS=0V	--	–	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V, VDS=0V	--	–	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=-250μA	-1.0	-1.8	-2.5	V
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-10A	--	25	35	mΩ
		VGS=-4.5V, ID=-5A	--	38	50	mΩ
Dynamic Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
CISS	Input Capacitance	VDS=-30V, VGS=0V, f=1MHz	–	3880	–	pF
COSS	Output Capacitance		–	169	–	pF
CRSS	Reverse Transfer Capacitance		–	138	–	pF
Switching Characteristics						
Qg	Total Gate Charge	VDS=-30V, ID=-10A, VGS=-10V	–	111	–	nC
Qgs	Gate Source Charge		–	25	–	nC
Qgd	Gate Drain Charge		–	15.5	–	nC
td(on)	Turn-on Delay Time	VDD=-10V, ID=-10A, VGS=-10V, RG=6Ω	–	20	–	nS
tr	Turn-on Rise Time		–	25	–	nS
td(off)	Turn-Off Delay Time		–	71	–	nS
tf	Turn-Off Fall Time		–	30	–	nS
Source- Drain Diode Characteristics						
VSD	Forward on voltage	TJ=25°C, IS=-10A	--	–	-1.2	V

Typical Operating Characteristics

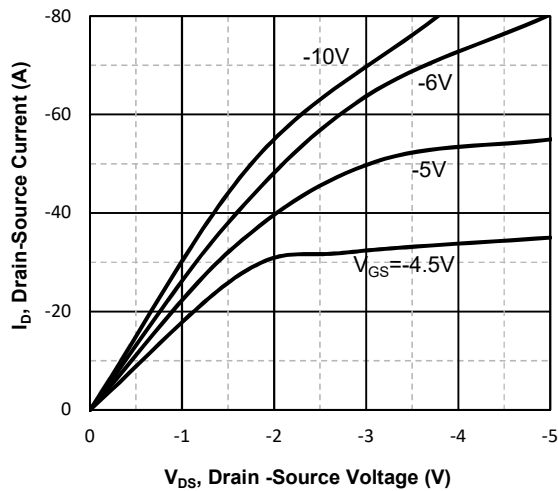


Fig1. Typical Output Characteristics

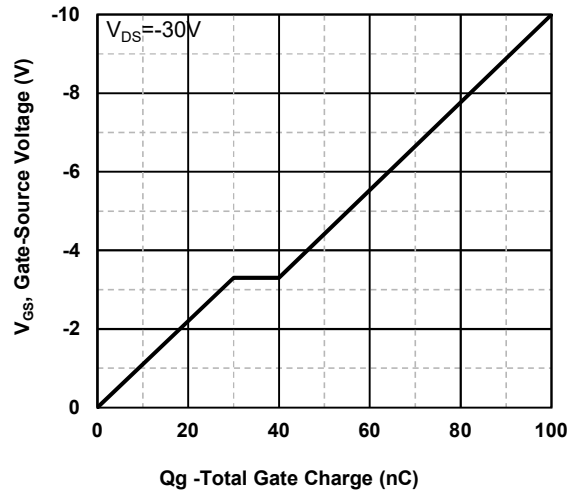


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

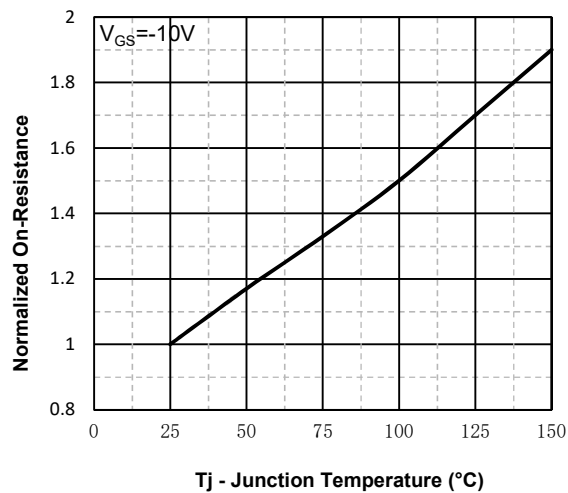


Fig3. Normalized On-Resistance Vs. Temperature

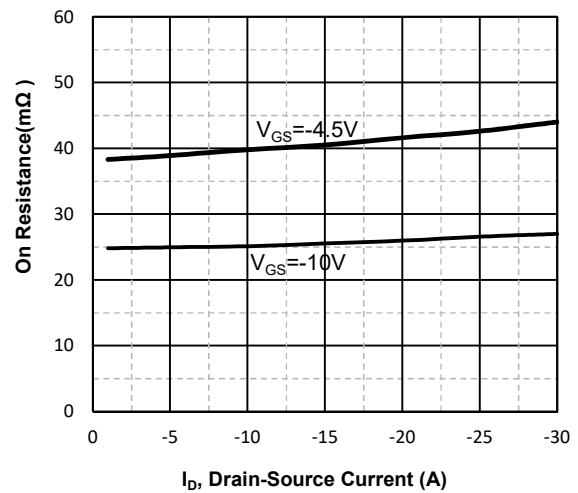


Fig4. Drain-Source on Resistance Vs. Drain-Source Current

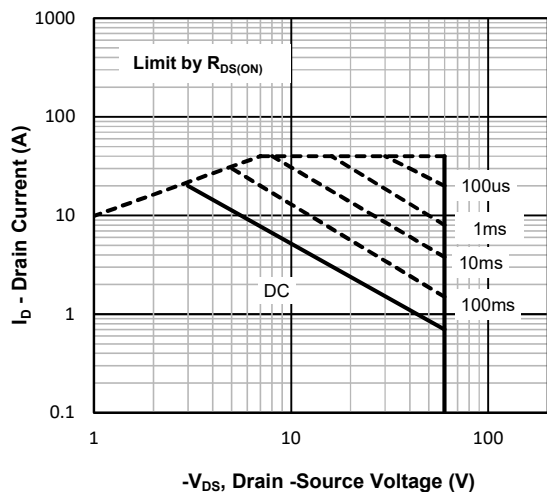


Fig5. Maximum Safe Operating Area

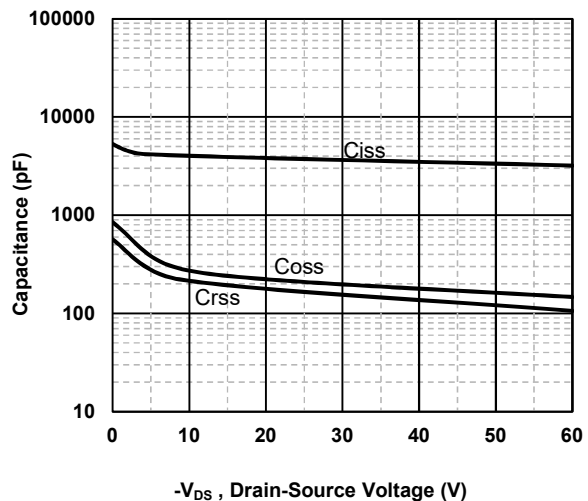
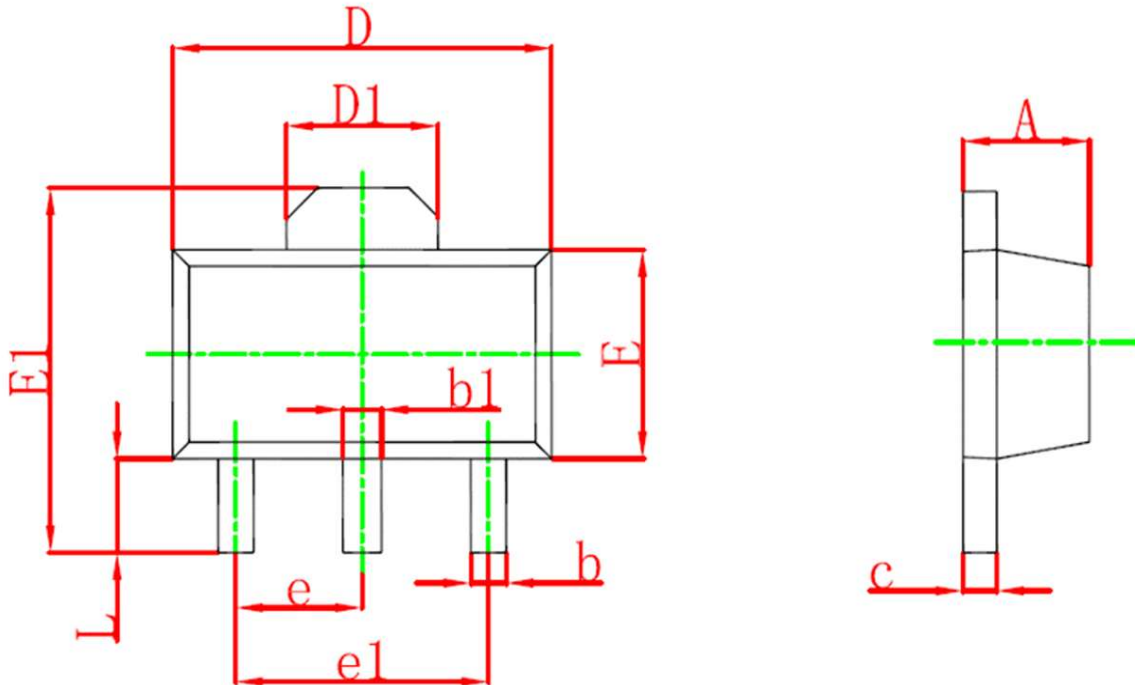


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-89-3L Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions in Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF		0.061 REF	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP		0.060 TYP	
e1	3.000 TYP		0.118 TYP	
L	0.900	1.200	0.035	0.047